

IRFR825TRPbF

HEXFET® Power MOSFET

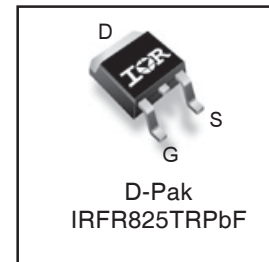
Applications

- Zero Voltage Switching SMPS
- Uninterruptible Power Supplies
- Motor Control applications

V_{DSS}	$R_{DS(on)}$ typ.	T_{rr} typ.	I_D
500V	1.05 Ω	92ns	6.0A

Features and Benefits

- Fast body diode eliminates the need for external diodes in ZVS applications.
- Lower Gate charge results in simpler drive requirements.
- Higher Gate voltage threshold offers improved noise immunity.



Absolute Maximum Ratings

	Parameter	Max.	Units
I_D @ $T_C = 25^\circ\text{C}$	Continuous Drain Current, V_{GS} @ 10V	6.0	A
I_D @ $T_C = 100^\circ\text{C}$	Continuous Drain Current, V_{GS} @ 10V	3.9	
I_{DM}	Pulsed Drain Current ①	24	
P_D @ $T_C = 25^\circ\text{C}$	Power Dissipation	119	W
	Linear Derating Factor	1.0	W/ $^\circ\text{C}$
V_{GS}	Gate-to-Source Voltage	± 20	V
dv/dt	Peak Diode Recovery dv/dt ③	9.9	V/ns
T_J	Operating Junction and	-55 to + 150	$^\circ\text{C}$
T_{STG}	Storage Temperature Range		
	Soldering Temperature, for 10 seconds	300 (1.6mm from case)	

Diode Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
I_S	Continuous Source Current (Body Diode)	—	—	6.0	A	MOSFET symbol showing the integral reverse p-n junction diode.
I_{SM}	Pulsed Source Current (Body Diode) ①	—	—	24		
V_{SD}	Diode Forward Voltage	—	—	1.2	V	$T_J = 25^\circ\text{C}$, $I_S = 6.0\text{A}$, $V_{GS} = 0\text{V}$ ④
t_{rr}	Reverse Recovery Time	—	92	138	ns	$T_J = 25^\circ\text{C}$, $I_F = 6.0\text{A}$
		—	152	228		$T_J = 125^\circ\text{C}$, $di/dt = 100\text{A}/\mu\text{s}$ ④
Q_{rr}	Reverse Recovery Charge	—	167	251	nC	$T_J = 25^\circ\text{C}$, $I_S = 6.0\text{A}$, $V_{GS} = 0\text{V}$ ④
		—	292	438		$T_J = 125^\circ\text{C}$, $di/dt = 100\text{A}/\mu\text{s}$ ④
I_{RRM}	Reverse Recovery Current	—	3.6	5.4	A	$T_J = 25^\circ\text{C}$, $I_S = 6.0\text{A}$, $V_{GS} = 0\text{V}$ $di/dt = 100\text{A}/\mu\text{s}$ ④
t_{on}	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by $LS+LD$)				

Notes ① through ⑦ are on page 2

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Static @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	500	—	—	V	$V_{GS} = 0V, I_D = 250\mu A$
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	0.33	—	V/ $^\circ\text{C}$	Reference to 25°C , $I_D = 1mA$
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	1.05	1.3	Ω	$V_{GS} = 10V, I_D = 3.7A$ ④
$V_{GS(th)}$	Gate Threshold Voltage	3.0	—	5.0	V	$V_{DS} = V_{GS}, I_D = 250\mu A$
I_{DSS}	Drain-to-Source Leakage Current	—	—	25	μA	$V_{DS} = 500V, V_{GS} = 0V$
		—	—	2.0	mA	$V_{DS} = 400V, V_{GS} = 0V, T_J = 125^\circ\text{C}$
I_{GSS}	Gate-to-Source Forward Leakage	—	—	100	nA	$V_{GS} = 20V$
	Gate-to-Source Reverse Leakage	—	—	-100	nA	$V_{GS} = -20V$

Dynamic @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
g_{fs}	Forward Transconductance	7.5	—	—	S	$V_{DS} = 50V, I_D = 3.7A$
Q_g	Total Gate Charge	—	—	34	nC	$I_D = 6.0A$
Q_{gs}	Gate-to-Source Charge	—	—	11	nC	$V_{DS} = 400V$
Q_{gd}	Gate-to-Drain ("Miller") Charge	—	—	14	nC	$V_{GS} = 10V$, See Fig.14a & 14b ④
$t_{d(on)}$	Turn-On Delay Time	—	8.5	—	ns	$V_{DD} = 250V$
t_r	Rise Time	—	25	—	ns	$I_D = 6.0A$
$t_{d(off)}$	Turn-Off Delay Time	—	30	—	ns	$R_G = 7.5\Omega$
t_f	Fall Time	—	20	—	ns	$V_{GS} = 10V$, See Fig. 15a & 15b ④
C_{iss}	Input Capacitance	—	1346	—	pF	$V_{GS} = 0V$
C_{oss}	Output Capacitance	—	76	—	pF	$V_{DS} = 25V$
C_{rss}	Reverse Transfer Capacitance	—	15	—	pF	$f = 1.0KHz$, See Fig. 5
C_{oss}	Output Capacitance	—	1231	—	pF	$V_{GS} = 0V, V_{DS} = 1.0V, f = 1.0MHz$
C_{oss}	Output Capacitance	—	25	—	pF	$V_{GS} = 0V, V_{DS} = 400V, f = 1.0MHz$
$C_{oss \text{ eff.}}$	Effective Output Capacitance	—	51	—	pF	
$C_{oss \text{ eff. (ER)}}$	Effective Output Capacitance (Energy Related)	—	43	—	pF	$V_{GS} = 0V, V_{DS} = 0V \text{ to } 400V$ ⑤

Avalanche Characteristics

	Parameter	Typ.	Max.	Units
E_{AS}	Single Pulse Avalanche Energy ②	—	178	mJ
I_{AR}	Avalanche Current ①	—	3	A
E_{AR}	Repetitive Avalanche Energy ①	—	11.9	mJ

Thermal Resistance

	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case ⑥	—	1.05	$^\circ\text{C/W}$
$R_{\theta JA}$	Junction-to-Ambient (PCB Mount) ⑦	—	50	$^\circ\text{C/W}$
$R_{\theta JA}$	Junction-to-Ambient	—	110	$^\circ\text{C/W}$

Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature. (See Fig. 11)
- ② Starting $T_J = 25^\circ\text{C}$, $L = 40mH$, $R_G = 25\Omega$, $I_{AS} = 3.0A$. (See Figure 13).
- ③ $I_{SD} = 6.0A$, $di/dt \leq 416A/\mu s$, $V_{DD} V_{(BR)DSS}$, $T_J \leq 150^\circ\text{C}$.
- ④ Pulse width $\leq 300\mu s$; duty cycle $\leq 2\%$.

- ⑤ $C_{oss \text{ eff.}}$ is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 to 80% V_{DSS} . $C_{oss \text{ eff. (ER)}}$ is a fixed capacitance that stores the same energy as C_{oss} while V_{DS} is rising from 0 to 80% V_{DSS} .
- ⑥ R_{θ} is measured at T_J approximately 90°C
- ⑦ When mounted on 1" square PCB (FR-4 or G-10 Material). For recommended footprint and soldering technique refer to application note # AN- 994 techniques refer to application note #AN-994.

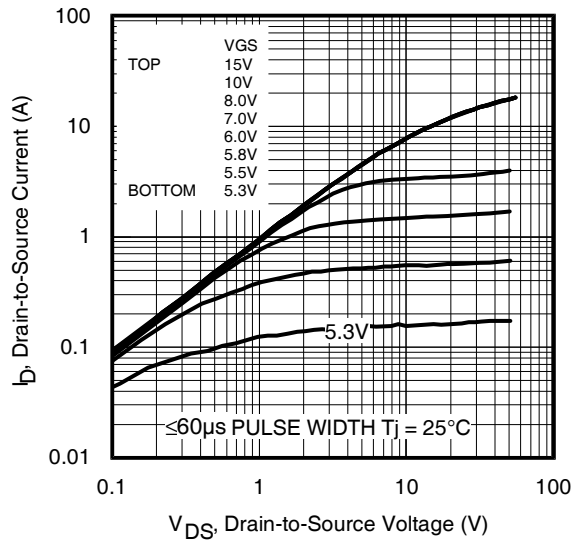


Fig 1. Typical Output Characteristics

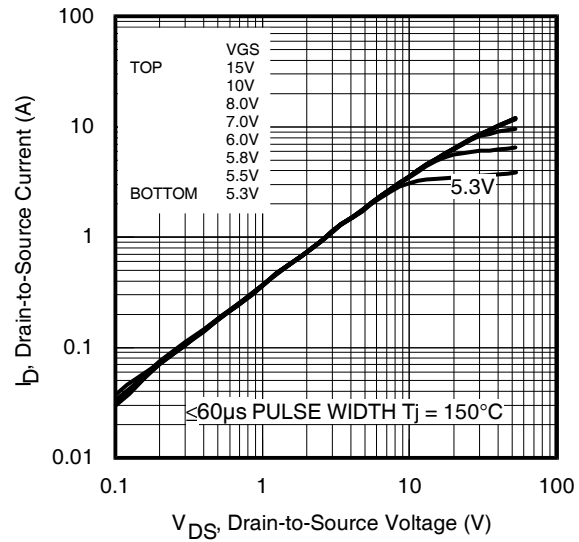


Fig 2. Typical Output Characteristics

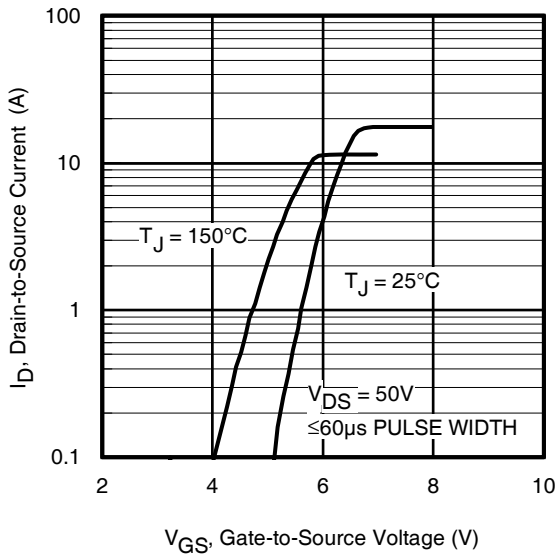


Fig 3. Typical Transfer Characteristics

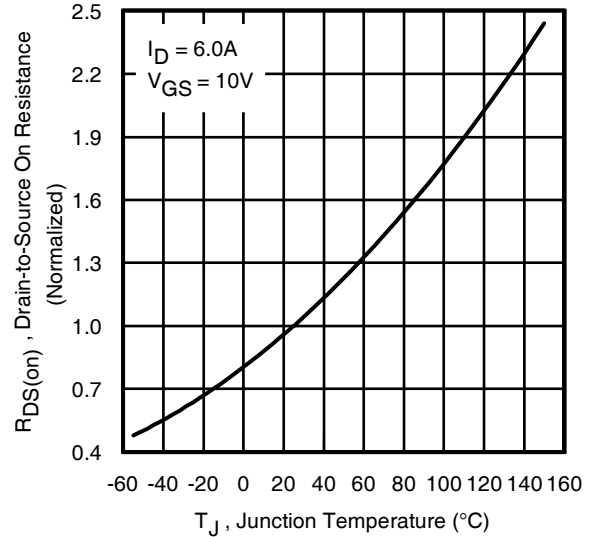
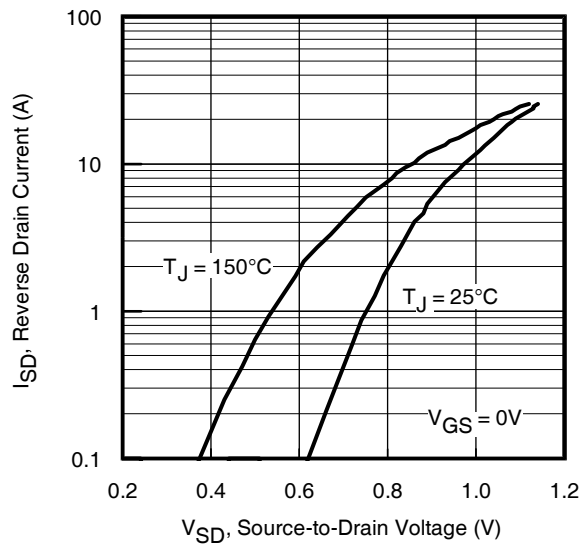
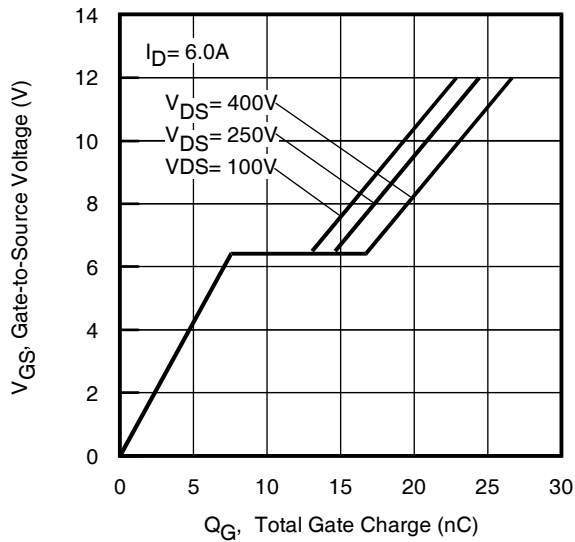
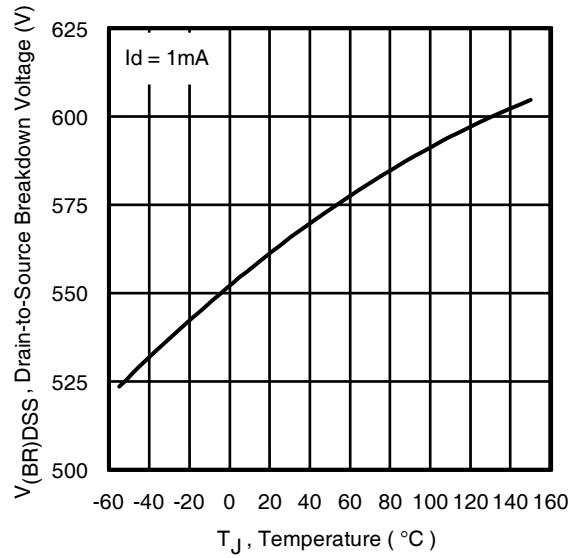
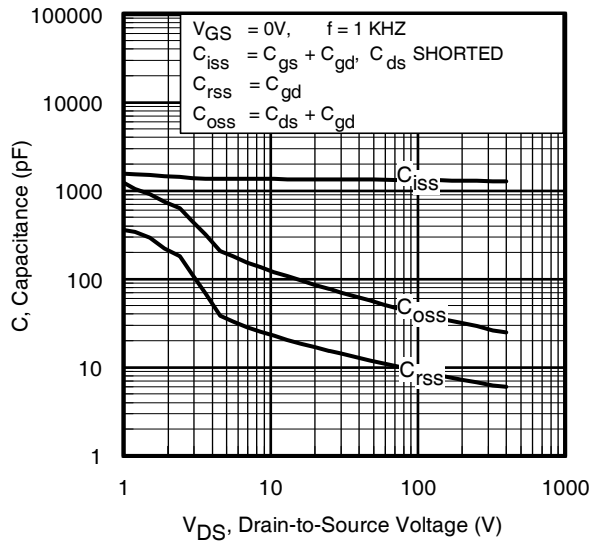


Fig 4. Normalized On-Resistance Vs. Temperature



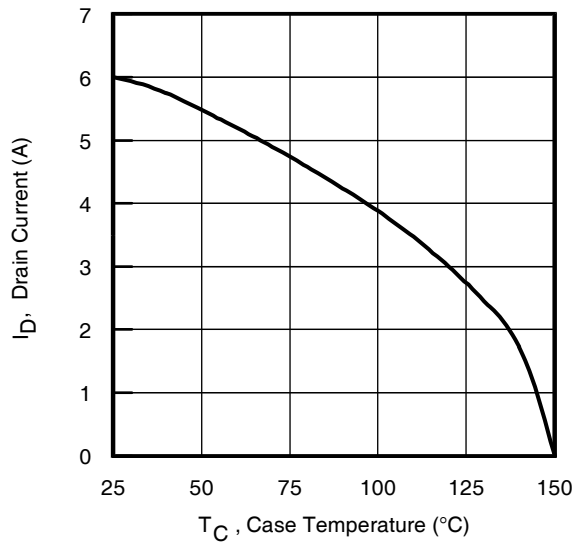


Fig 9. Maximum Drain Current Vs. Case Temperature

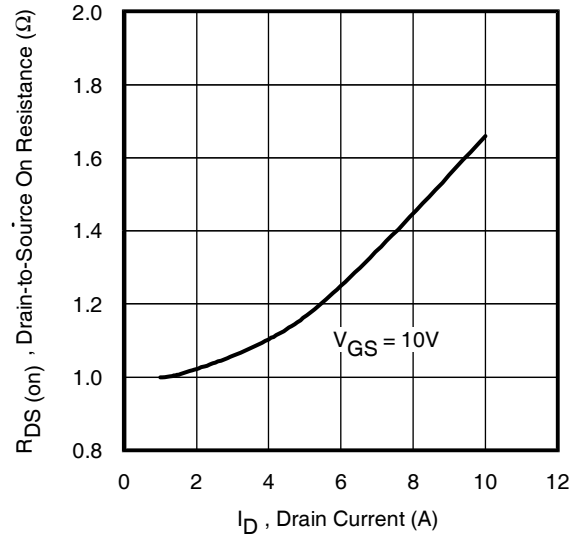


Fig 9. Typical $R_{DS(on)}$ Vs. Drain Current

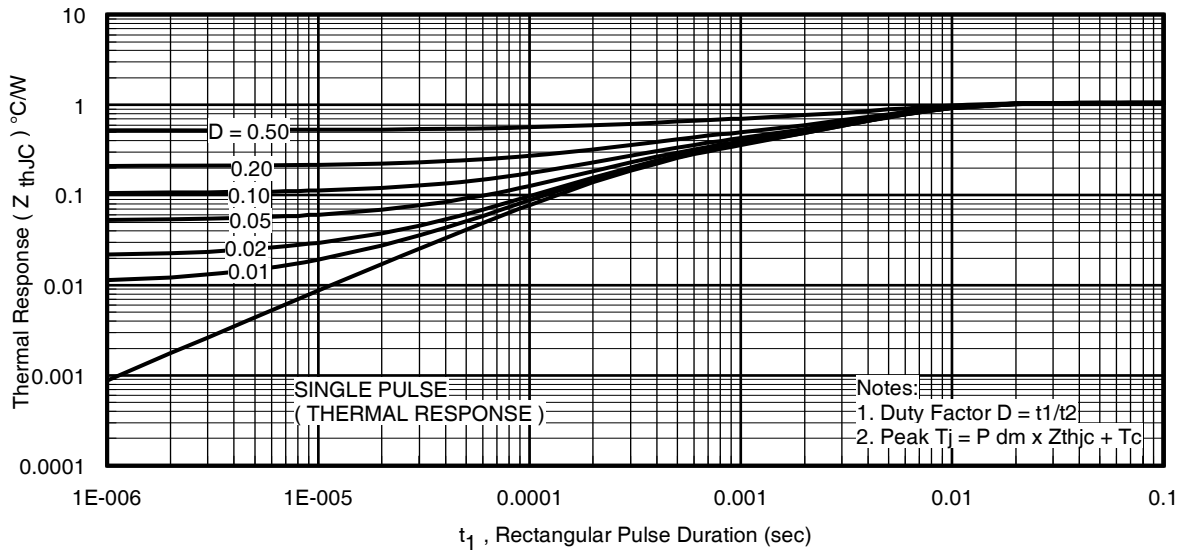
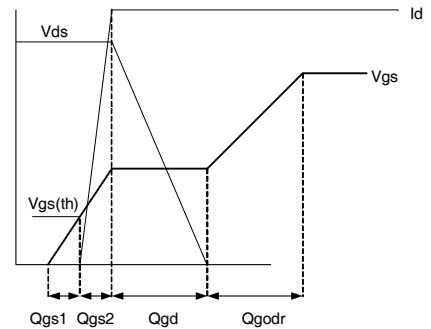
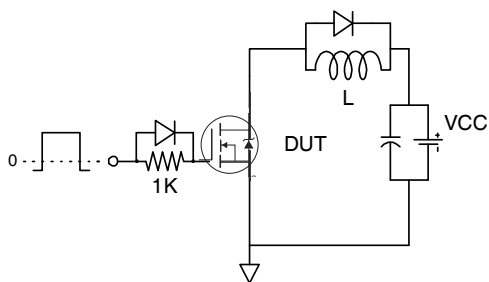
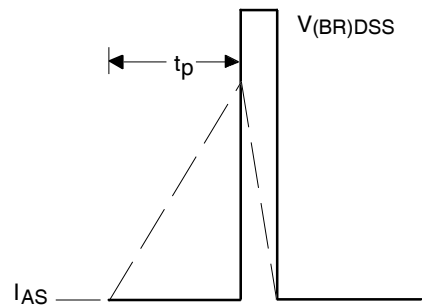
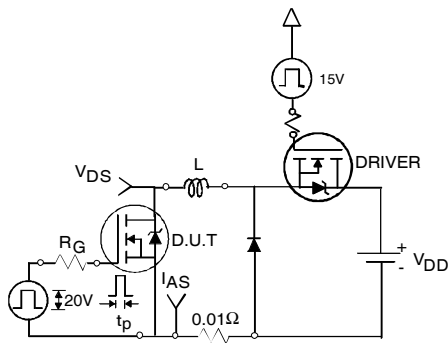
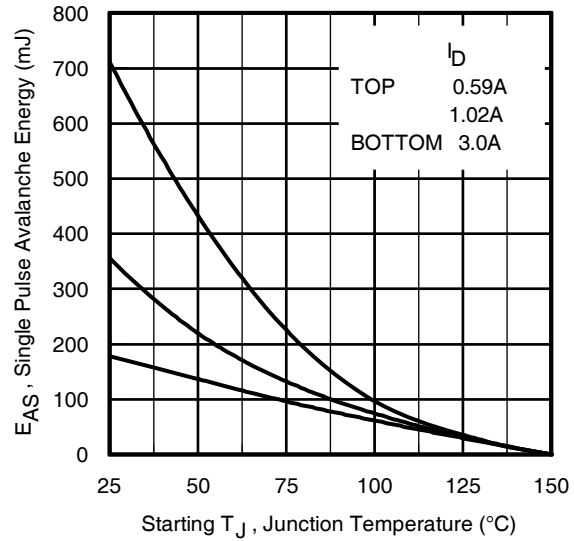
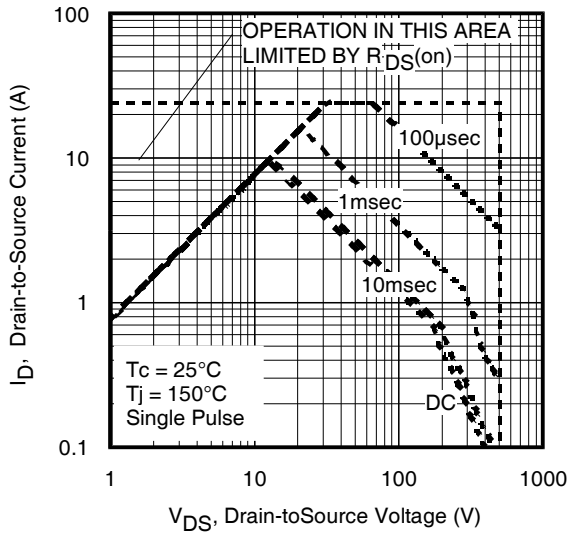


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Case

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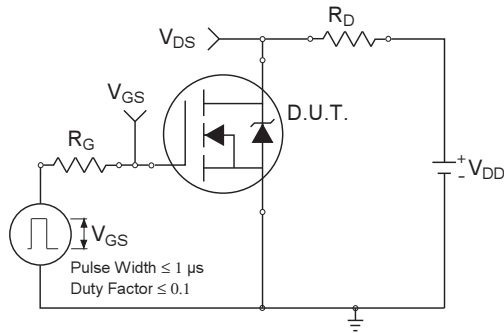


Fig 15a. Switching Time Test Circuit

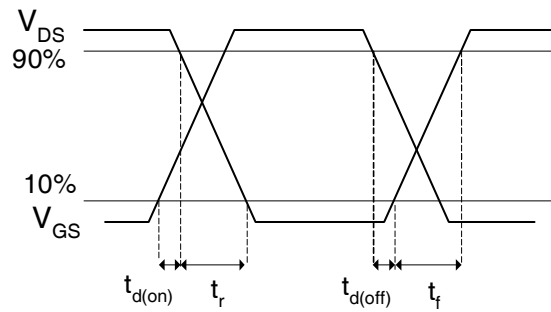


Fig 15b. Switching Time Waveforms

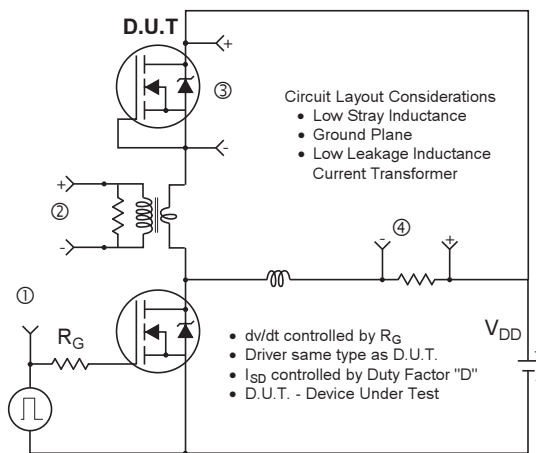
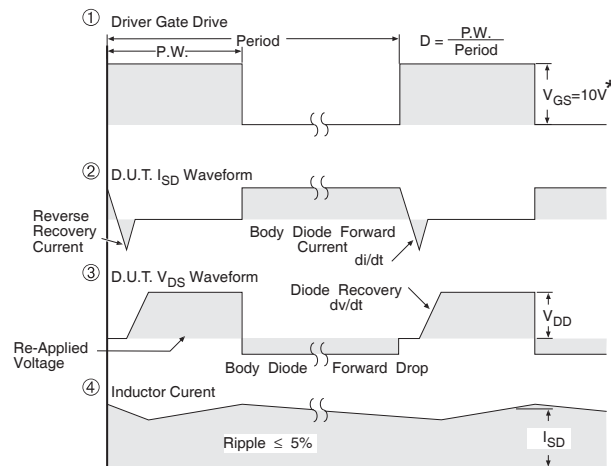


Fig 16. Peak Diode Recovery dv/dt Test Circuit for N-Channel
HEXFET® Power MOSFETs



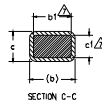
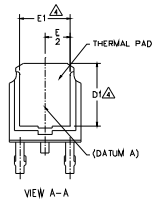
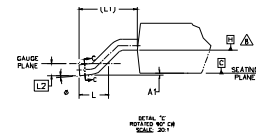
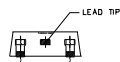
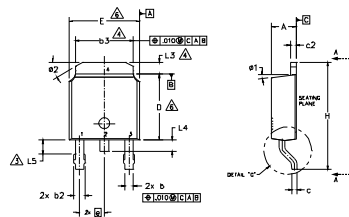
* $V_{GS} = 5V$ for Logic Level Devices

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D-Pak (TO-252AA) Package Outline

Dimensions are shown in millimeters (inches)



- NOTES:
- 1- DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994
 - 2- DIMENSIONS ARE SHOWN IN INCHES [MILLIMETERS]
 - 3- LEAD DIMENSION UNCONTROLLED IN L5.
 - 4- DIMENSION D1, E1, L3 & b3 ESTABLISH A MINIMUM MOUNTING SURFACE FOR THERMAL PAD.
 - 5- SECTION C-C DIMENSIONS APPLY TO THE FLAT SECTION OF THE LEAD BETWEEN .005 AND 0.10 [0.13 AND 0.25] FROM THE LEAD TIP.
 - 6- DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED .005 [0.13] PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTMOST EXTREMES OF THE PLASTIC BODY.
 - 7- DIMENSION b1 & c1 APPLIED TO BASE METAL ONLY.
 - 8- DATUM A & B TO BE DETERMINED AT DATUM PLANE H.
 - 9- OUTLINE CONFORMS TO JEDEC OUTLINE TO-252AA.

SYMBOL	DIMENSIONS				NOTES
	MILLIMETERS		INCHES		
	MIN.	MAX.	MIN.	MAX.	
A	2.18	2.39	.086	.094	
A1	-	0.13	-	.005	
b	0.64	0.89	.025	.035	
b1	0.65	0.79	.025	.031	7
b2	0.76	1.14	.030	.045	
b3	4.95	5.46	.195	.216	4
c	0.46	0.61	.018	.024	
c1	0.41	0.56	.016	.022	7
c2	0.46	0.89	.018	.035	
D	5.97	6.22	.235	.245	6
D1	5.21	-	.205	-	4
E	6.35	6.73	.250	.265	6
E1	4.32	-	.170	-	4
e	2.29 BSC		.090 BSC		
H	9.40	10.41	.370	.410	
L	1.40	1.78	.055	.070	
L1	2.74 BSC		.108 REF.		
L2	0.51 BSC		.020 BSC		
L3	0.89	1.27	.035	.050	4
L4	-	1.02	-	.040	
L5	1.14	1.52	.045	.060	3
e	0°	15°	0°	15°	
e1	0°	15°	0°	15°	
#2	25°	35°	25°	35°	

LEAD ASSIGNMENTS

HEXFET

- 1.- GATE
- 2.- DRAIN
- 3.- SOURCE
- 4.- DRAIN

IGBT & CoPAK

- 1.- GATE
- 2.- COLLECTOR
- 3.- EMITTER
- 4.- COLLECTOR

D-Pak (TO-252AA) Part Marking Information

EXAMPLE: THIS IS AN IRFR120
WITH ASSEMBLY
LOT CODE 1234
ASSEMBLED ON WW 16, 2001
IN THE ASSEMBLY LINE "A"

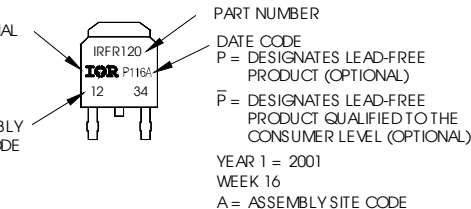
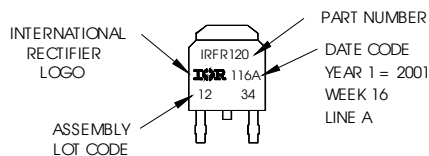
Note: "P" in assembly line position
indicates "Lead-Free"

"P" in assembly line position indicates
"Lead-Free" qualification to the consumer-level

OR

INTERNATIONAL
RECTIFIER
LOGO

ASSEMBLY
LOT CODE

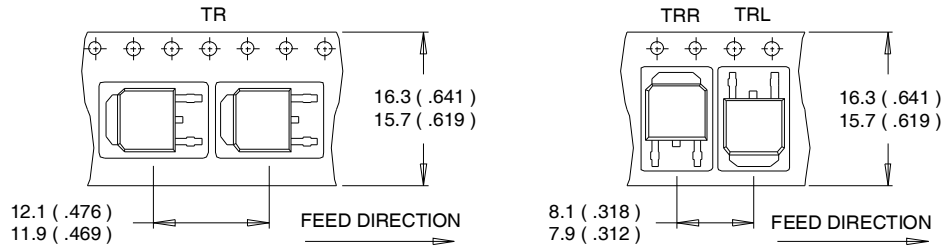


YEAR 1 = 2001
WEEK 16
A = ASSEMBLY SITE CODE

Note: For the most current drawing please refer to IR website at <http://www.irf.com/package/>

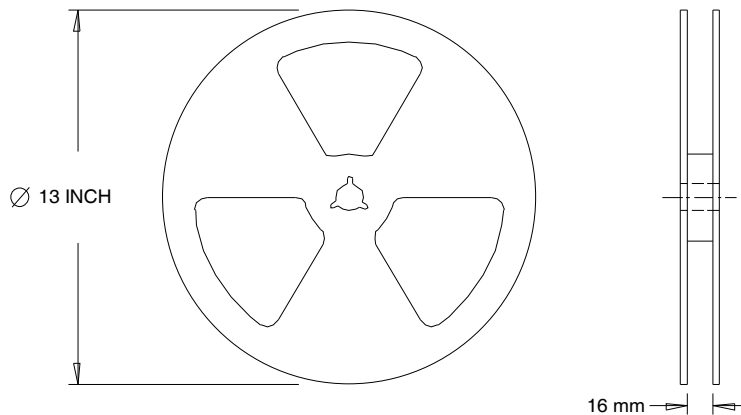
D-Pak (TO-252AA) Tape & Reel Information

Dimensions are shown in millimeters (inches)



NOTES :

1. CONTROLLING DIMENSION : MILLIMETER.
2. ALL DIMENSIONS ARE SHOWN IN MILLIMETERS (INCHES).
3. OUTLINE CONFORMS TO EIA-481 & EIA-541.



NOTES :

1. OUTLINE CONFORMS TO EIA-481.

Data and specifications subject to change without notice.
This product has been designed and qualified for the Industrial market.
Qualification Standards can be found on IR's Web site.

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TAC Fax: (310) 252-7903

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